

PJM08DN40PA

Dual N-Channel Enhancement Mode Power MOSFET

Product Summary

- $V_{DS} = 40V, I_D = 8A$
- $R_{DS(on)} < 20m\Omega @ V_{GS} = 10V$
- $R_{DS(on)} < 27m\Omega @ V_{GS} = 4.5V$

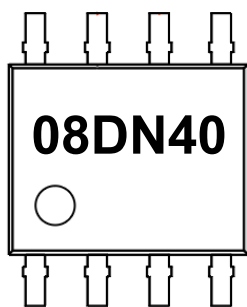
Features

- Advanced Trench Technology
- 100% Avalanche Tested
- RoHS and Reach Compliant
- Halogen and Antimony Free
- Moisture Sensitivity Level 3

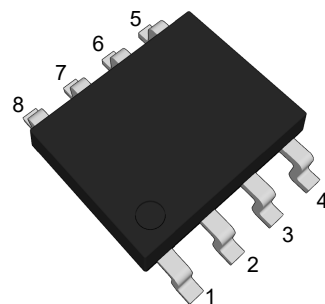
Application

- Wireless Charging
- Boost Driver
- Brushless Motor

Marking Code



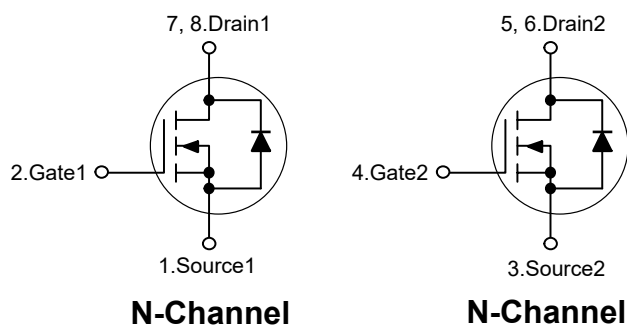
SOP-8



(Top View)

Pin	Description	Pin	Description
1	Source1	4	Gate2
2	Gate1	5,6	Drain2
3	Source2	7,8	Drain1

Schematic Diagram



Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	8	A
Drain Current-Pulsed ^{Note1}	I_{DM}	36	A
Maximum Power Dissipation	P_D	2.1	W
Single Pulse Avalanche Energy ^{Note2}	E_{AS}	25	mJ
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient ^{Note3}	$R_{\theta JA}$	59.5	°C/W
--	-----------------	------	------



PJM08DN40PA

Dual N-Channel Enhancement Mode Power MOSFET

Electrical Characteristics

($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	40	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	--	--	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	--	--	± 100	nA
Gate Threshold Voltage ^{Note4}	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.7	2.5	V
Drain-Source On-Resistance ^{Note4}	$R_{DS(on)}$	$V_{GS}=10V, I_D=7A$	--	14	20	m Ω
		$V_{GS}=4.5V, I_D=6A$	--	19	27	m Ω
Forward Transconductance ^{Note4}	g_{FS}	$V_{DS}=5V, I_D=1A$	--	5.1	--	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=20V, V_{GS}=0V, f=1\text{MHz}$	--	1021	--	pF
Output Capacitance	C_{oss}		--	87	--	pF
Reverse Transfer Capacitance	C_{rss}		--	67	--	pF
Gate Resistance	R_g	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	--	1	--	Ω
Total Gate Charge	Q_g	$V_{DS}=20V, I_D=5A,$ $V_{GS}=10V$	--	14	--	nC
Gate-Source Charge	Q_{gs}		--	4	--	nC
Gate-Drain Charge	Q_{gd}		--	4.5	--	nC
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, I_D=5A,$ $V_{GS}=10V, R_{GEN}=3\Omega$	--	10	--	nS
Turn-on Rise Time	t_r		--	12	--	nS
Turn-off Delay Time	$t_{d(off)}$		--	33	--	nS
Turn-off Fall Time	t_f		--	10	--	nS
Source-Drain Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=8A$	--	--	1.2	V
Diode Forward Current	I_S		--	--	8	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. EAS Condition: $T_J=25^\circ\text{C}, V_{DD}=20V, V_G=10V, R_G=25\Omega, L=0.5\text{mH}, I_{AS}=10A$.

3. Surface Mounted on FR4 Board, $t \leq 10$ sec.

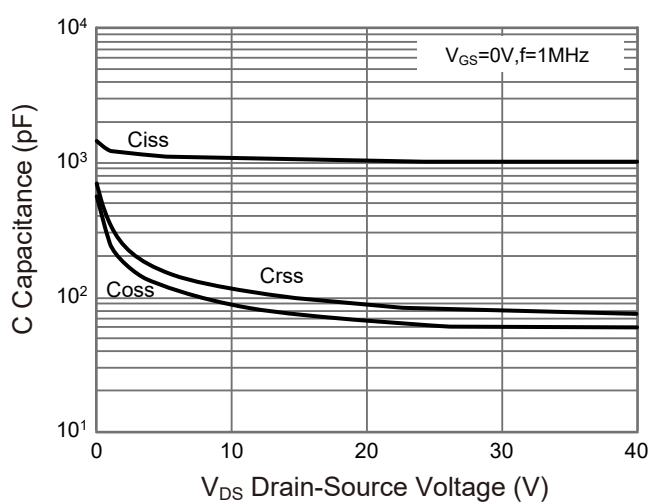
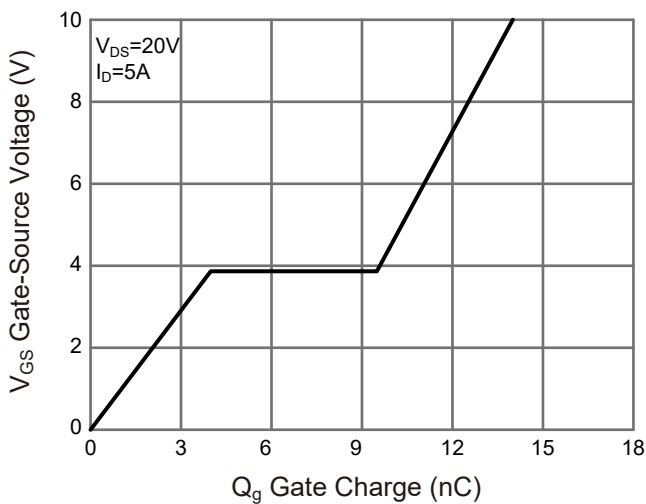
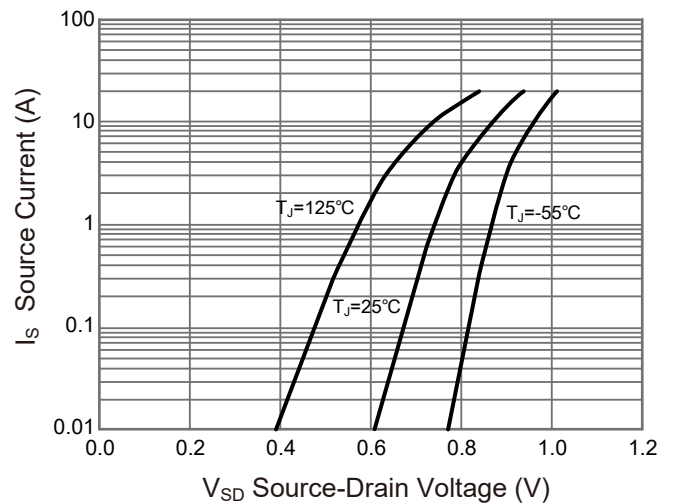
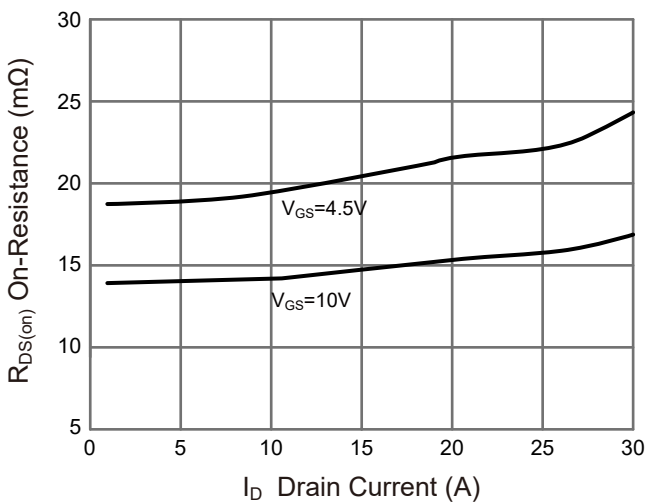
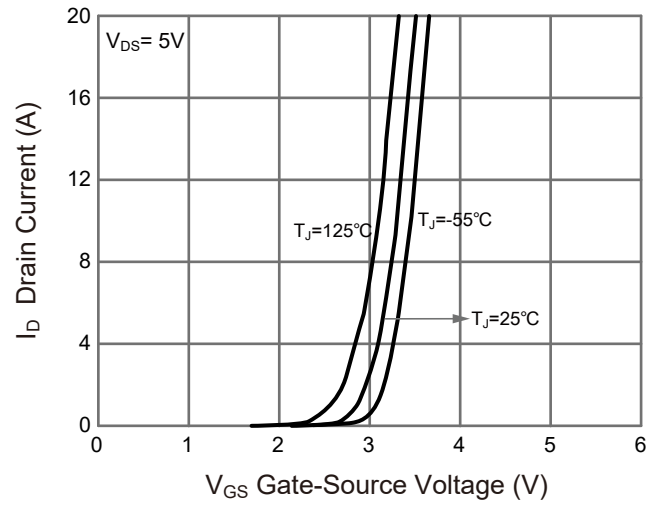
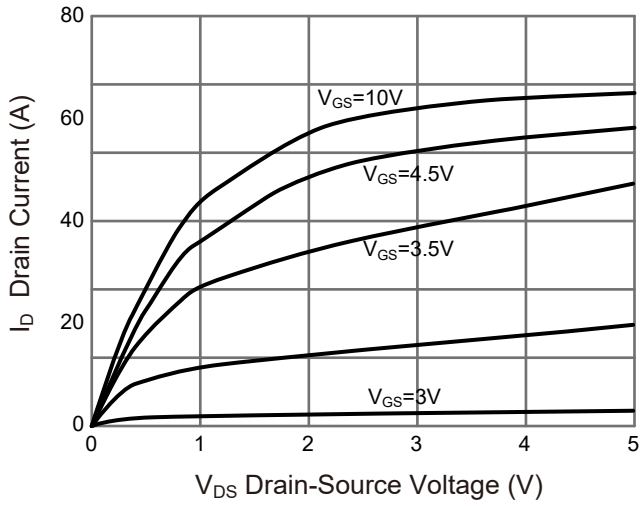
4. Pulse Test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.



PJM08DN40PA

Dual N-Channel Enhancement Mode Power MOSFET

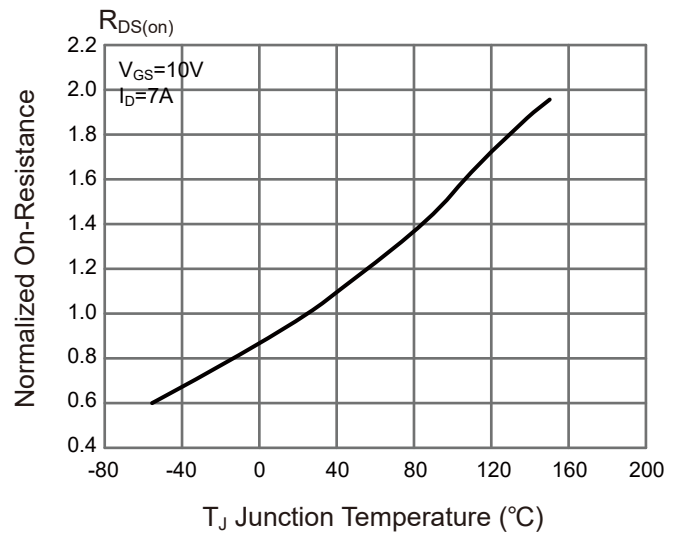
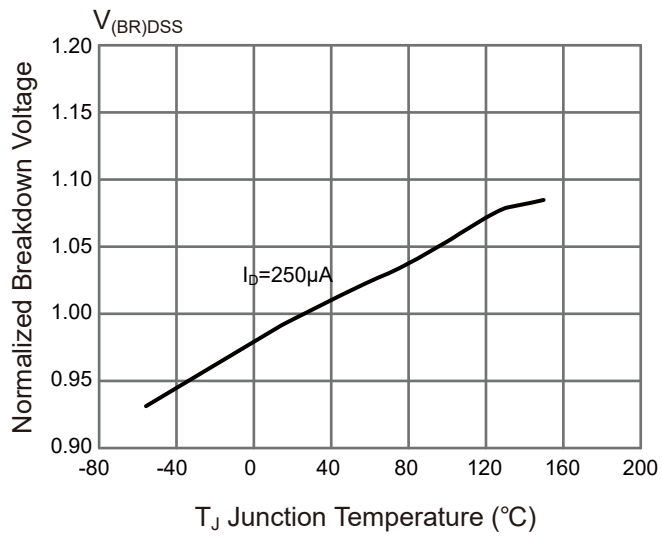
Typical Characteristic Curves





PJM08DN40PA

Dual N-Channel Enhancement Mode Power MOSFET





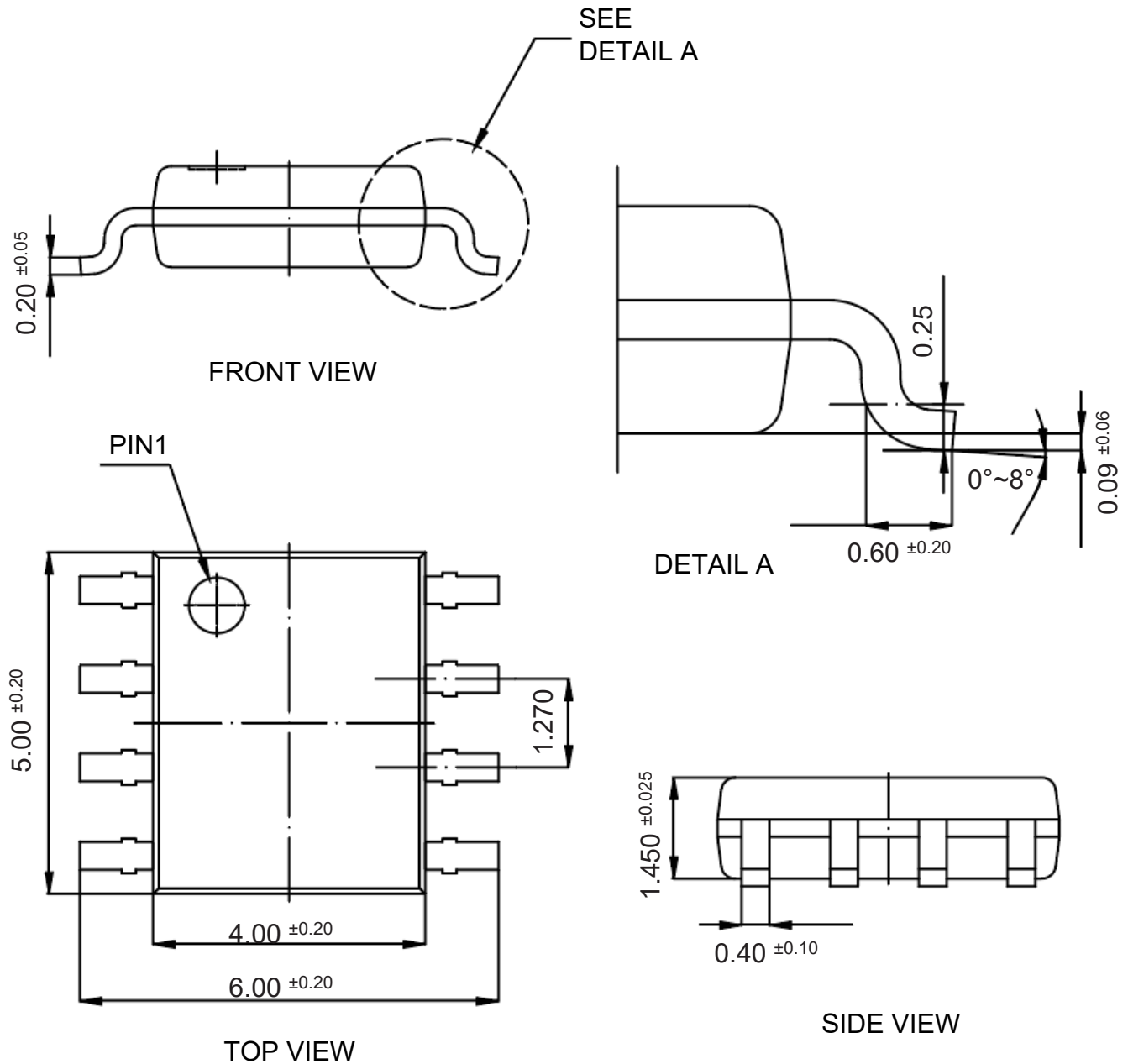
PJM08DN40PA

Dual N-Channel Enhancement Mode Power MOSFET

Package Outline

SOP-8

Dimensions in mm



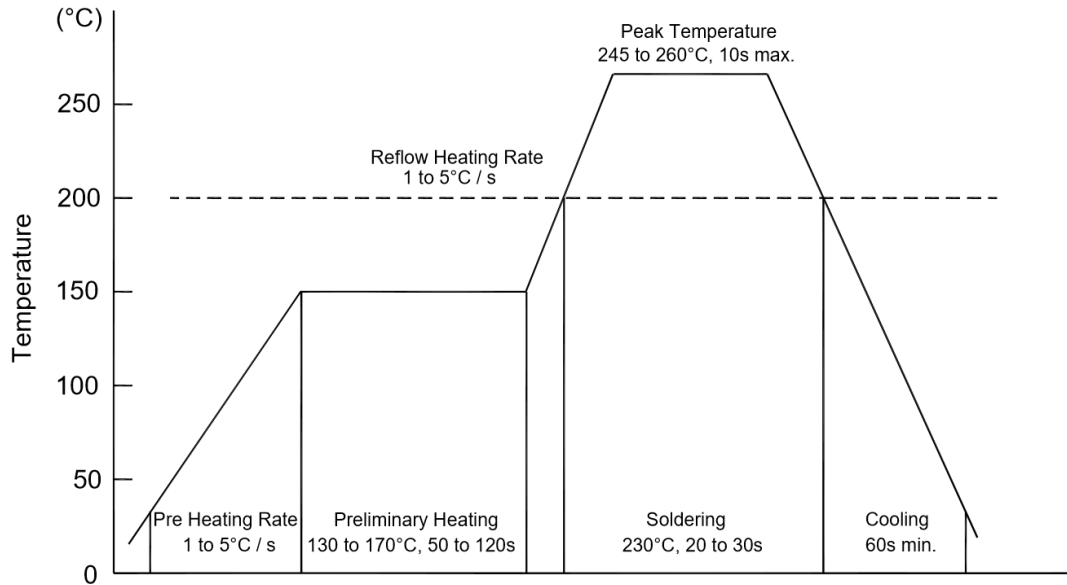
Ordering Information

Device	Package	Shipping
PJM08DN40PA	SOP-8	4,000PCS/Reel&13inches



Conditions of Soldering and Storage

◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245°C. If peak temperature is below 245°C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

◆ Conditions of hand soldering

- Temperature: 300°C
- Time: 3s max.
- Times: one time

◆ Storage conditions

- **Temperature**
5 to 40°C
- **Humidity**
30 to 80% RH
- **Recommended period**
One year after manufacturing

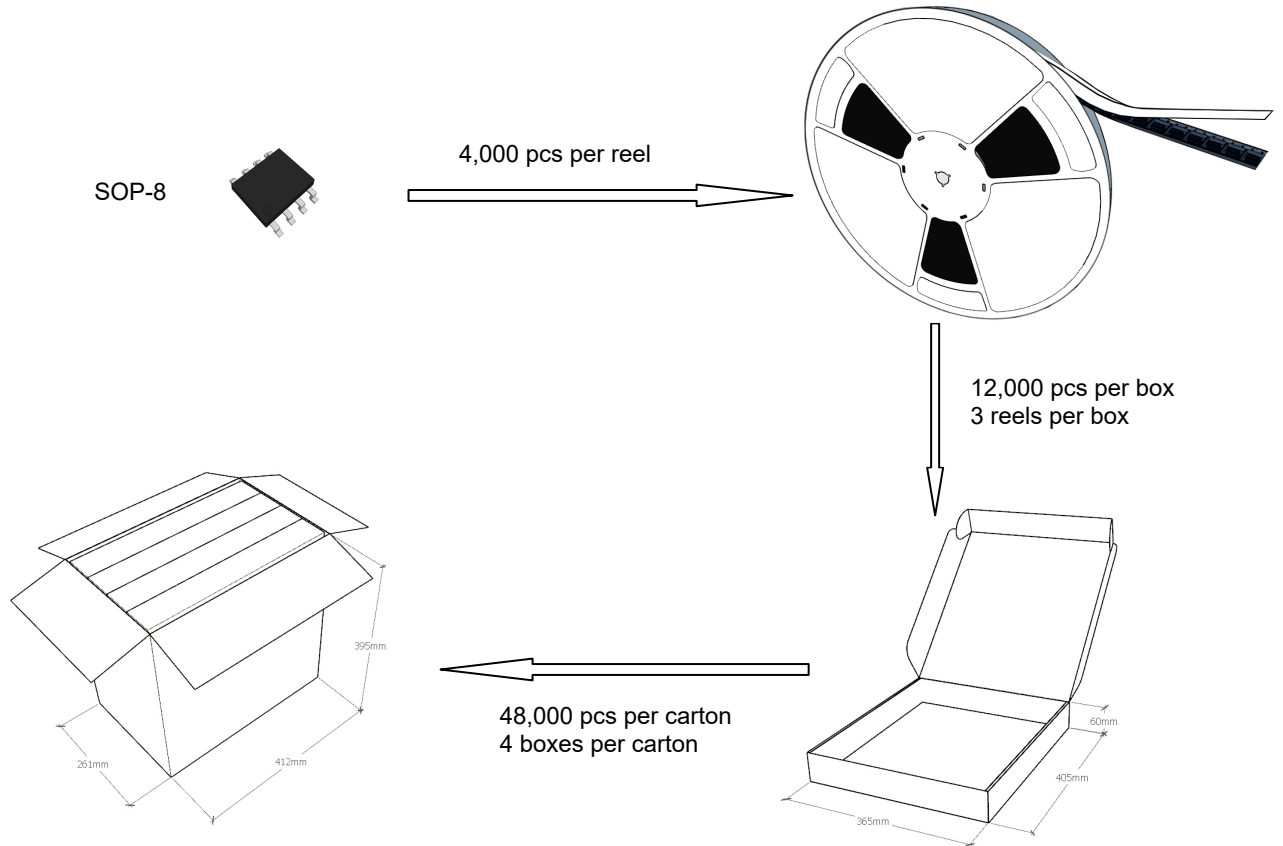


PJM08DN40PA

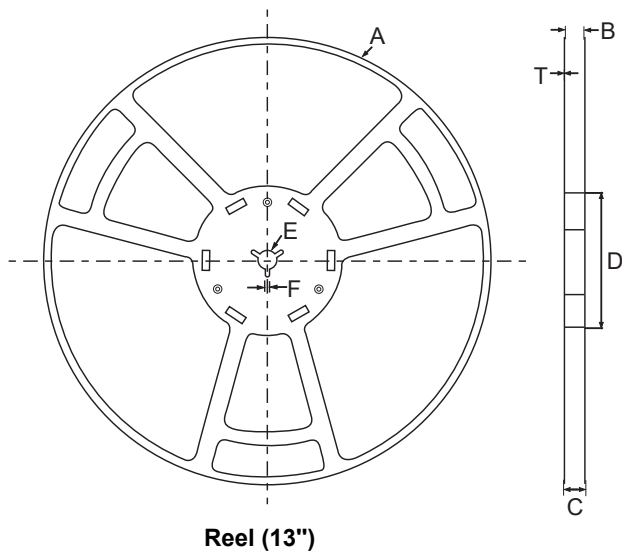
Dual N-Channel Enhancement Mode Power MOSFET

Package Specifications

- The method of packaging



◆ Embossed tape and reel data



symbol	Value(unit:mm)
A	$\phi 330 \pm 1$
B	12.7 ± 0.5
C	16.5 ± 0.3
D	$\phi 99.5 \pm 0.5$
E	$\phi 13.6 \pm 0.3$
F	2.8 ± 0.3
T	1.9 ± 0.2

